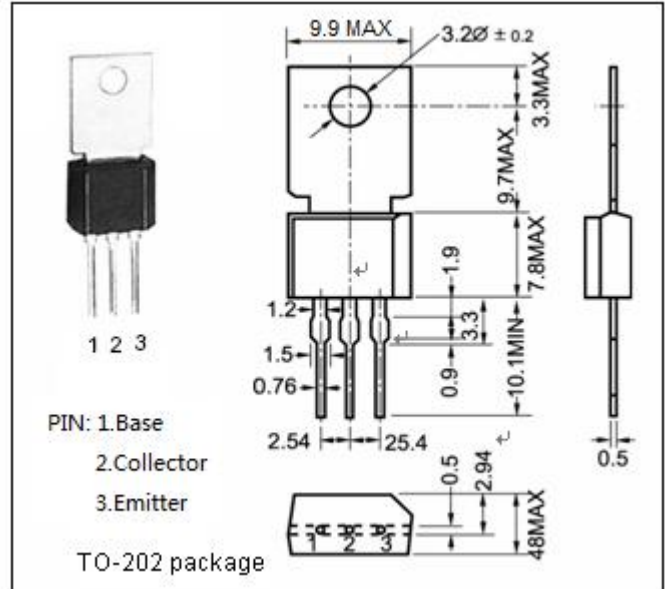


isc Silicon NPN Power Transistor
2SC1848
DESCRIPTION

- Silicon NPN epitaxial planar
- High voltage
- Complement to Type 2SA887
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for medium power amplifier


ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	70	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	2	A
P _C	Total Power Dissipation @ T _a =25°C	1.2	w
	Total Power Dissipation @ T _C =25°C	10	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

isc Silicon NPN Power Transistor**2SC1848****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.1\text{A}$			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=40\text{V}; I_E=0$			1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE-1}	DC Current Gain	$I_C=0.1\text{A}; V_{CE}=5\text{V}$	30			
h_{FE-2}	DC Current Gain	$I_C=1.0\text{A}; V_{CE}=5\text{V}$	50		220	
f_T	Current-Gain—Bandwidth Product	$I_C=500\text{mA}; V_{CE}=5\text{V}$		150		MHz

◆ **h_{FE-2} Classifications**

P	Q	R
50-100	80-160	120-220